Half-Bridge Driver

Features

- Floating channel designed for bootstrap operation
- Fully operational to +600V
- Tolerant to negative transient voltage
- dV/dt immune
- Gate drive supply range from 10 to 20V
- Undervoltage lockout for both channels
- 3.3V, 5V and 15V input logic compatible
- Cross-conduction prevention logic
- Matched propagation delay for both channels
- Outputs in phase with inputs
- Logic and power ground +/-5V offset
- Internal 540ns dead-time
- Lower di/dt gate driver for better noise immunity

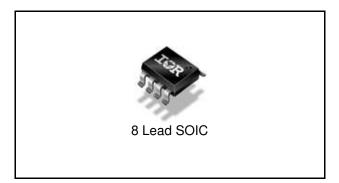
Description

The IR25606 is a high voltage, high speed power MOSFET and IGBT driver with independent high and low side referenced output channels. Proprietary HVIC and latch immune CMOS technologies enable ruggedized monolithic construction. The logic input is compatible with standard CMOS or LSTTL output, down to 3.3V logic. The output drivers feature a high pulse current buffer stage designed for minimum driver cross-conduction. The floating channel can be used to drive an N-channel power MOSFET or IGBT in the high side configuration which operates up to 600 V.

Product Summary

VOFFSET	600V max.
I _{O+/-}	200 mA / 350 mA
V _{OUT}	10 – 20V
Ton/off (typ.)	220 & 200 ns
Dead time (typ.)	540 ns

Package Options

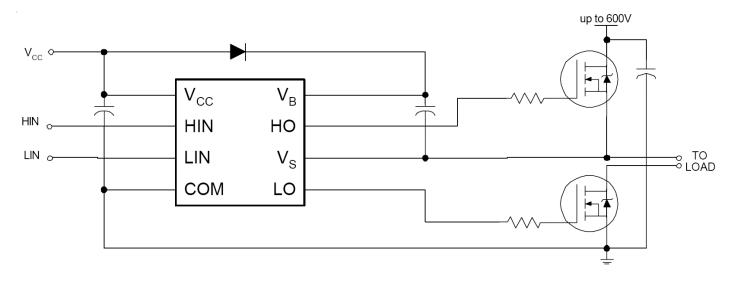


Ordering Information

Dees Deut Number		Standard Pack		Standard Pack		Ordereble Dert Number	
Base Part Number	Package Type	Form	Quantity	Orderable Part Number			
IR25606SPBF	SO8N	Tube	95	IR25606SPBF			
IR25606SPBF	SO8N	Tape and Reel	2500	IR25606STRPBF			



Typical Connection Diagram





Absolute Maximum Ratings

Absolute maximum ratings indicate sustained limits beyond which damage to the device may occur. All voltage parameters are absolute voltages referenced to COM. The thermal resistance and power dissipation ratings are measured under board mounted and still air conditions.

Symbol	Definition	Min.	Max.	Units
VB	High side floating absolute voltage	-0.3	625	
Vs	High side floating supply offset voltage	V _B - 25	V _B + 0.3	
V _{HO}	High side floating output voltage	V _S - 0.3	V _B + 0.3	v
V _{CC}	Low side and logic fixed supply voltage	-0.3	25	, i i i i i i i i i i i i i i i i i i i
V _{LO}	Low side output voltage	-0.3	V _{CC} + 0.3	
V _{IN}	Logic input voltage (HIN & LIN)	-0.3	V _{CC} + 0.3	
dVs/dt	Allowable offset supply voltage transient		50	V/ns
PD	Package power dissipation @ $T_A \le +25^{\circ}C$	—	0.625	w
Rth _{JA}	Thermal resistance, junction to ambient	_	200	°C/W
TJ	Junction temperature	_	150	
Τ _S	Storage temperature	-55	150	°C
TL	Lead temperature (soldering, 10 seconds)		300	

Recommended Operating Conditions

For proper operation the device should be used within the recommended conditions. The V_S offset rating is tested with all supplies biased at 15V differential.

Symbol	Definition	Min.	Max.	Units
VB	High side floating supply absolute voltage	V _S + 10	V _S + 20	
VS	High side floating supply offset voltage	+	600	
V _{HO}	High side floating output voltage	Vs	VB	v
V _{CC}	Low side and logic fixed supply voltage	10	20	
V _{LO}	Low side output voltage	0	V _{CC}	
V _{IN}	Logic input voltage	0	V _{CC}	
T _A	Ambient temperature	-40	125	°C

⁺ Logic operational for VS of -5 to +600V. Logic state held for VS of -5V to -VBS. (Please refer to Design Tip DT97-3 for more details).

Dynamic Electrical Characteristics

 $V_{BIAS}~(V_{CC},~V_{BS})$ = 15V, CL = 1000 pF and T_A = 25°C unless otherwise specified.

Symbol	Definition	Min.	Тур.	Max.	Units	Test Conditions
ton	Turn-on propagation delay	—	220	300		$V_{S} = 0V$
toff	Turn-off propagation delay	_	200	280		$V_{\rm S}$ = 0V or 600V
tr	Turn-on rise time	—	150	220	ne	$V_{S} = 0V$
tf	Turn-off fall time	—	50	80	ns	$V_{\rm S} = 0V$
DT	Deadtime	400	540	680		
MT	Delay matching, HS & LS turn-on/off	_	0	46		

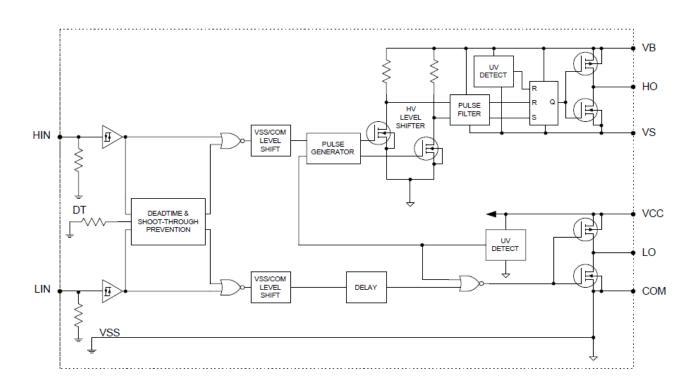
Static Electrical Characteristics

 V_{BIAS} (V_{CC} , V_{BS}) = 15V and T_A = 25°C unless otherwise specified. The V_{IN} , V_{TH} and I_{IN} parameters are referenced to COM. The V_O and I_O parameters are referenced to COM and are applicable to the respective output leads: HO and LO.

Symbol	Definition	Min.	Тур.	Max.	Units	Test Conditions
VIH	Logic "1" input voltage	2.9	—	_		V _{CC} = 10V to 20V
V _{IL}	Logic "0" input voltage	—		0.8		$V_{CC} = 10V$ to 20V
V _{OH}	High level output voltage, V _{BIAS} - V _O	—	0.8	1.4	V	I _O = 20 mA
V _{OL}	Low level output voltage, V _O	—	0.3	0.6		l _O = 20 mA
I _{LK}	Offset supply leakage current	—		50		$V_{B} = V_{S} = 600V$
I _{QBS}	Quiescent V _{BS} supply current	20	60	150	μA	$V_{IN} = 0V \text{ or } 5V$
lacc	Quiescent V _{CC} supply current	0.4	1.0	1.6	mA	$V_{IN} = 0V \text{ or } 5V$
I _{IN+}	Logic "1" input bias current	—	5	20	μA	$V_{IN} = 5V$
I _{IN-}	Logic "0" input bias current	—	1	2	μ. ι	$V_{IN} = 0V$
V _{CCUV+} V _{BSUV+}	V_{CC} and V_{BS} supply undervoltage positive going threshold	8	8.9	10		
V _{CCUV-} V _{BSUV-}	V_{CC} and V_{BS} supply undervoltage negative going threshold	7.4	8.2	9	V	
V _{CCUVH} V _{BSUVH}	Hysteresis	0.3	0.7			
I _{O+}	Output high short circuit pulsed current	97	200	_	- mA	V _O = 0V PW ≤ 10 µs
I _{O-}	Output low short circuit pulsed current	250	350	_		V _O = 15V PW ≤ 10 µs



Functional Block Diagram

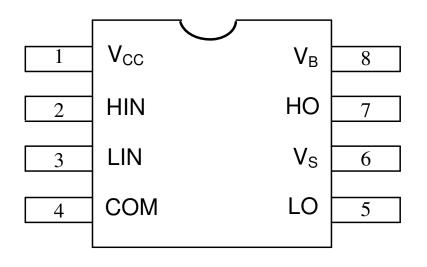




Lead Definitions

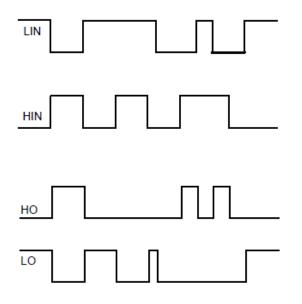
Symbol	Description	
HIN	Logic input for high side gate driver outputs (HO), in phase	
LIN	Logic input for low side gate driver outputs (LO), in phase	
VB	High side floating supply	
HO	High side gate drive output	
VS	High side floating supply return	
V _{CC}	Low side and logic fixed supply	
LO	Low side gate drive output	
COM	Low side return	

Lead Assignments





Application Information and Additional Details



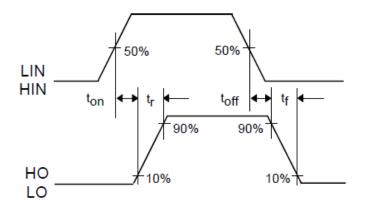




Figure 1. Input/Output Timing Diagram

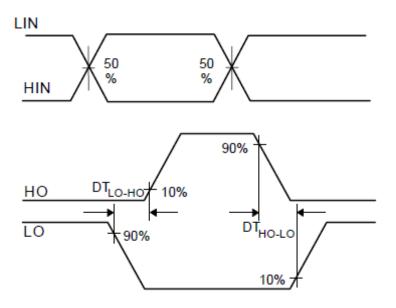
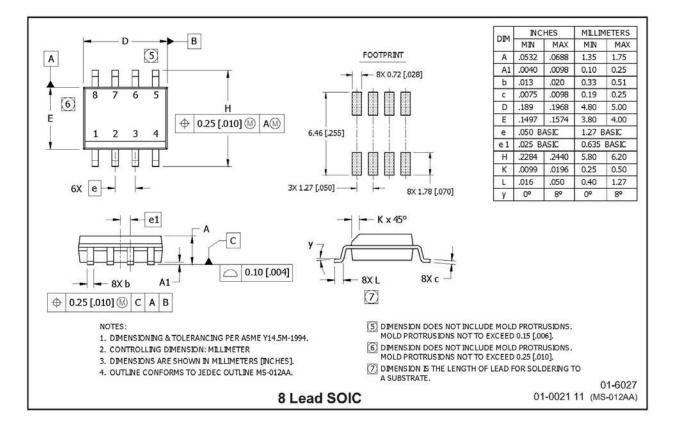


Figure 3. Deadtime Waveform Definitions

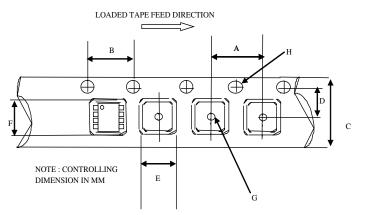


Package Details



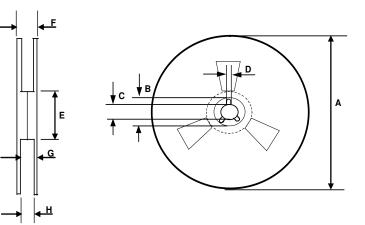


Tape and Reel Details



CARRIER TAPE DIMENSION FOR 8SOICN

	Me	tric	Imp	erial
Code	Min	Max	Min	Max
A	7.90	8.10	0.311	0.318
В	3.90	4.10	0.153	0.161
С	11.70	12.30	0.46	0.484
D	5.45	5.55	0.214	0.218
E	6.30	6.50	0.248	0.255
F	5.10	5.30	0.200	0.208
G	1.50	n/a	0.059	n/a
Н	1.50	1.60	0.059	0.062

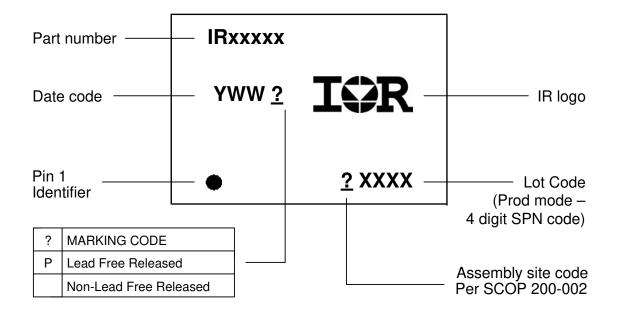


REEL DIMENSIONS FOR 8SOICN

	Me	etric	Imp	erial
Code	Min	Max	Min	Max
A	329.60	330.25	12.976	13.001
В	20.95	21.45	0.824	0.844
С	12.80	13.20	0.503	0.519
D	1.95	2.45	0.767	0.096
E	98.00	102.00	3.858	4.015
F	n/a	18.40	n/a	0.724
G	14.50	17.10	0.570	0.673
Н	12.40	14.40	0.488	0.566



Part Marking Information



Qualification Information[†]

Qualification Level	Industrial ^{††}	
	(per JEDEC JESD 47)	
	Comments: This family of ICs has passed JEDEC's	
	Industrial qualification. IR's Consumer qualification level is	
	granted by extension of the higher Industrial level.	
Majatura Canaitivity Laval	MSL2 ^{†††}	
Moisture Sensitivity Level	(per IPC/JEDEC J-STD-020)	
RoHS Compliant	Yes	

- † Qualification standards can be found at International Rectifier's web site http://www.irf.com/
- ++ Higher qualification ratings may be available should the user have such requirements. Please contact your International Rectifier sales representative for further information.
- +++ Higher MSL ratings may be available for the specific package types listed here. Please contact your International Rectifier sales representative for further information.

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